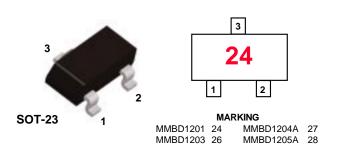
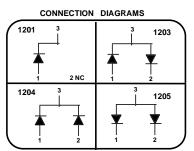


Discrete POWER & Signal **Technologies**

MMBD1201 / 1203 / 1204 / 1205





High Conductance Ultra Fast Diode

Sourced from Process 1P.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W _{IV}	Working Inverse Voltage	50	V
Io	Average Rectified Current	200	mA
I _F	DC Forward Current	600	mA
i _f	Recurrent Peak Forward Current	700	mA
İf(surge)	Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond	1.0 2.0	A A
T _{stg}	Storage Temperature Range	-55 to +150	°C
TJ	Operating Junction Temperature	150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MMBD1201/1203/1204/1205*	
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

^{*}Device mounted on glass epoxy PCB 1.6" X 1.6" X 0.06"; mounting pad for the collector lead min. 0.93 in2

High Conductance Ultra Fast Diode

(continued)

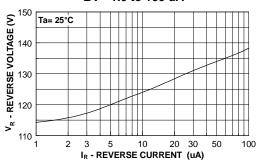
Electrical Characteristics

TA = 25°C unless otherwise noted

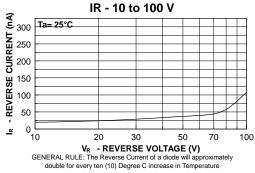
Symbol	Parameter	Test Conditions	Min	Max	Units
B_V	Breakdown Voltage	$I_R = 100 \mu A$	100		V
I _R	Reverse Current	V _R = 20 V V _R = 50 V V _R = 50 V, T _A = 150°C		25 50 5.0	nA nA μA
V _F	Forward Voltage	I _F = 1.0 mA I _F = 10 mA I _F = 100 mA I _F = 200 mA I _F = 300 mA	550 660 820 0.87	600 740 920 1.0 1.1	mV mV mV V
Ст	Diode Capacitance	V _R = 0, f = 1.0 MHz		2.0	pF
T _{RR}	Reverse Recovery Time	$I_{RR} = 1.0 \text{ mA}, I_F = I_R = 10 \text{ mA},$ $R_L = 100\Omega$		4.0	nS

Typical Characteristics

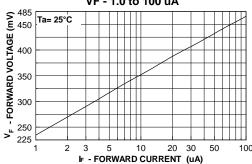
REVERSE VOLTAGE vs REVERSE CURRENT BV - 1.0 to 100 uA



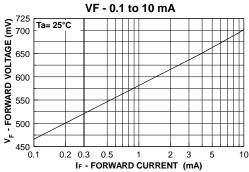
REVERSE CURRENT vs REVERSE VOLTAGE



FORWARD VOLTAGE vs FORWARD CURRENT VF - 1.0 to 100 uA



FORWARD VOLTAGE VS FORWARD CURRENT

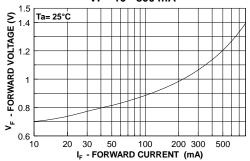


High Conductance Ultra Fast Diode

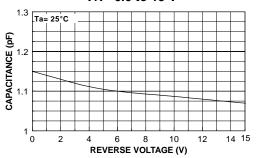
(continued)

Typical Characteristics (continued)

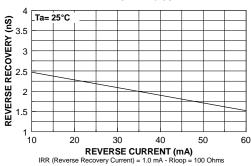
FORWARD VOLTAGE vs FORWARD CURRENT VF - 10 - 800 mA



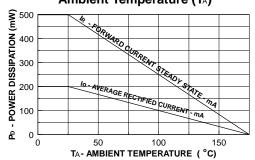
CAPACITANCE vs REVERSE VOLTAGE VR - 0.0 to 15 V



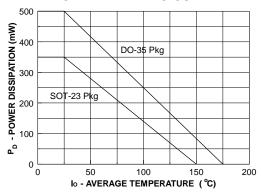
REVERSE RECOVERY TIME vs REVERSE CURRENT TRR - IR 10 mA vs 60 mA



Average Rectified Current (Io) & Forward Current (I_F) versus Ambient Temperature (T_A)



POWER DERATING CURVE



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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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